

Method and Circuit for Determining Sense Amplifier Sensitivity

ABSTRACT

5 A dynamic random access memory (DRAM) includes a bit line pair, including a first bit line and a second bit line. Memory cells and a sense amplifier are coupled to the bit lines. A first characterization cell is coupled between the first bit line and a first reference supply line. The first characterization cell includes a capacitor. Similarly, a second characterization cell is coupled between the first bit line and the first reference supply line. The second characterization cell also
10 includes a capacitor but preferably with a different capacitance. In the preferred embodiment, similar characterization cells are coupled to the second bit line.